

ABSTRACT

5 An object of the present invention is to provide a
flip-chip-type gallium nitride compound semiconductor
light-emitting device exhibiting excellent ohmic
characteristics, excellent bonding characteristics, and
high emission output.

10 The inventive flip-chip-type gallium nitride
compound semiconductor light-emitting device comprises a
positive electrode which has a three-layer structure
comprising an ohmic electrode layer composed of rhodium
which is in contact with the p-type semiconductor layer,
an adhesion layer composed of titanium which is provided
on the ohmic electrode layer and has a thickness of 10 Å
15 or more, and a bonding pad layer provided on the adhesion
layer and being composed of a metal selected from the
group consisting of gold, aluminum, nickel, and copper,
or composed of an alloy containing at least one of these
metals.